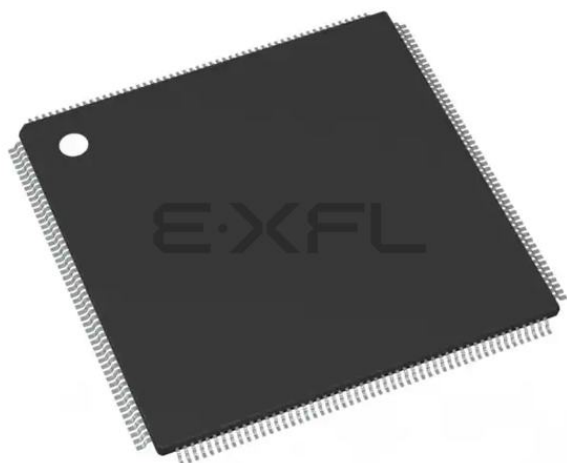




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Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M7
Core Size	32-Bit Single-Core
Speed	480MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I ² C, IrDA, LINbus, MDIO, MMC/SD/SDIO, QSPI, SAI, SPDIF, SPI, SWPMI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	168
Program Memory Size	2MB (2M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	1M x 8
Voltage - Supply (Vcc/Vdd)	1.62V ~ 3.6V
Data Converters	A/D 36x16b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	208-LQFP
Supplier Device Package	208-LQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32h753bit6

3 Functional overview

3.1 Arm® Cortex®-M7 with FPU

The Arm® Cortex®-M7 with double-precision FPU processor is the latest generation of Arm processors for embedded systems. It was developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and optimized power consumption, while delivering outstanding computational performance and low interrupt latency.

The Cortex®-M7 processor is a highly efficient high-performance featuring:

- Six-stage dual-issue pipeline
- Dynamic branch prediction
- Harvard architecture with L1 caches (16 Kbytes of I-cache and 16 Kbytes of D-cache)
- 64-bit AXI interface
- 64-bit ITCM interface
- 2x32-bit DTCM interfaces

The following memory interfaces are supported:

- Separate Instruction and Data buses (Harvard Architecture) to optimize CPU latency
- Tightly Coupled Memory (TCM) interface designed for fast and deterministic SRAM accesses
- AXI Bus interface to optimize Burst transfers
- Dedicated low-latency AHB-Lite peripheral bus (AHBP) to connect to peripherals.

The processor supports a set of DSP instructions which allow efficient signal processing and complex algorithm execution.

It also supports single and double precision FPU (floating point unit) speeds up software development by using metalanguage development tools, while avoiding saturation.

Figure 1 shows the general block diagram of the STM32H753xI family.

Note: Cortex®-M7 with FPU core is binary compatible with the Cortex®-M4 core.

3.2 Memory protection unit (MPU)

The memory protection unit (MPU) manages the CPU access rights and the attributes of the system resources. It has to be programmed and enabled before use. Its main purposes are to prevent an untrusted user program to accidentally corrupt data used by the OS and/or by a privileged task, but also to protect data processes or read-protect memory regions.

The MPU defines access rules for privileged accesses and user program accesses. It allows defining up to 16 protected regions that can in turn be divided into up to 8 independent subregions, where region address, size, and attributes can be configured. The protection area ranges from 32 bytes to 4 Gbytes of addressable memory.

When an unauthorized access is performed, a memory management exception is generated.

The boot loader is located in non-user System memory. It is used to reprogram the Flash memory through a serial interface (USART, I2C, SPI, USB-DFU). Refer to *STM32 microcontroller System memory Boot mode* application note (AN2606) for details.

3.5 Power supply management

3.5.1 Power supply scheme

STM32H53xI power supply voltages are the following:

- V_{DD} = 1.62 to 3.6 V: external power supply for I/Os, provided externally through V_{DD} pins.
- V_{DDLDO} = 1.62 to 3.6 V: supply voltage for the internal regulator supplying V_{CORE}
- V_{DDA} = 1.62 to 3.6 V: external analog power supplies for ADC, DAC, COMP and OPAMP.
- $V_{DD33USB}$ and $V_{DD50USB}$:
 $V_{DD50USB}$ can be supplied through the USB cable to generate the $V_{DD33USB}$ via the USB internal regulator. This allows supporting a V_{DD} supply different from 3.3 V.
 The USB regulator can be bypassed to supply directly $V_{DD33USB}$ if $V_{DD} = 3.3$ V.
- V_{BAT} = 1.2 to 3.6 V: power supply for the V_{SW} domain when V_{DD} is not present.
- V_{CAP} : V_{CORE} supply voltage, which values depend on voltage scaling (0.7 V, 0.9 V, 1.0 V, 1.1 V or 1.2 V). They are configured through VOS bits in PWR_D3CR register.
 The V_{CORE} domain is split into the following power domains that can be independently switch off.
 - D1 domain containing some peripherals and the Cortex®-M7 core.
 - D2 domain containing a large part of the peripherals.
 - D3 domain containing some peripherals and the system control.

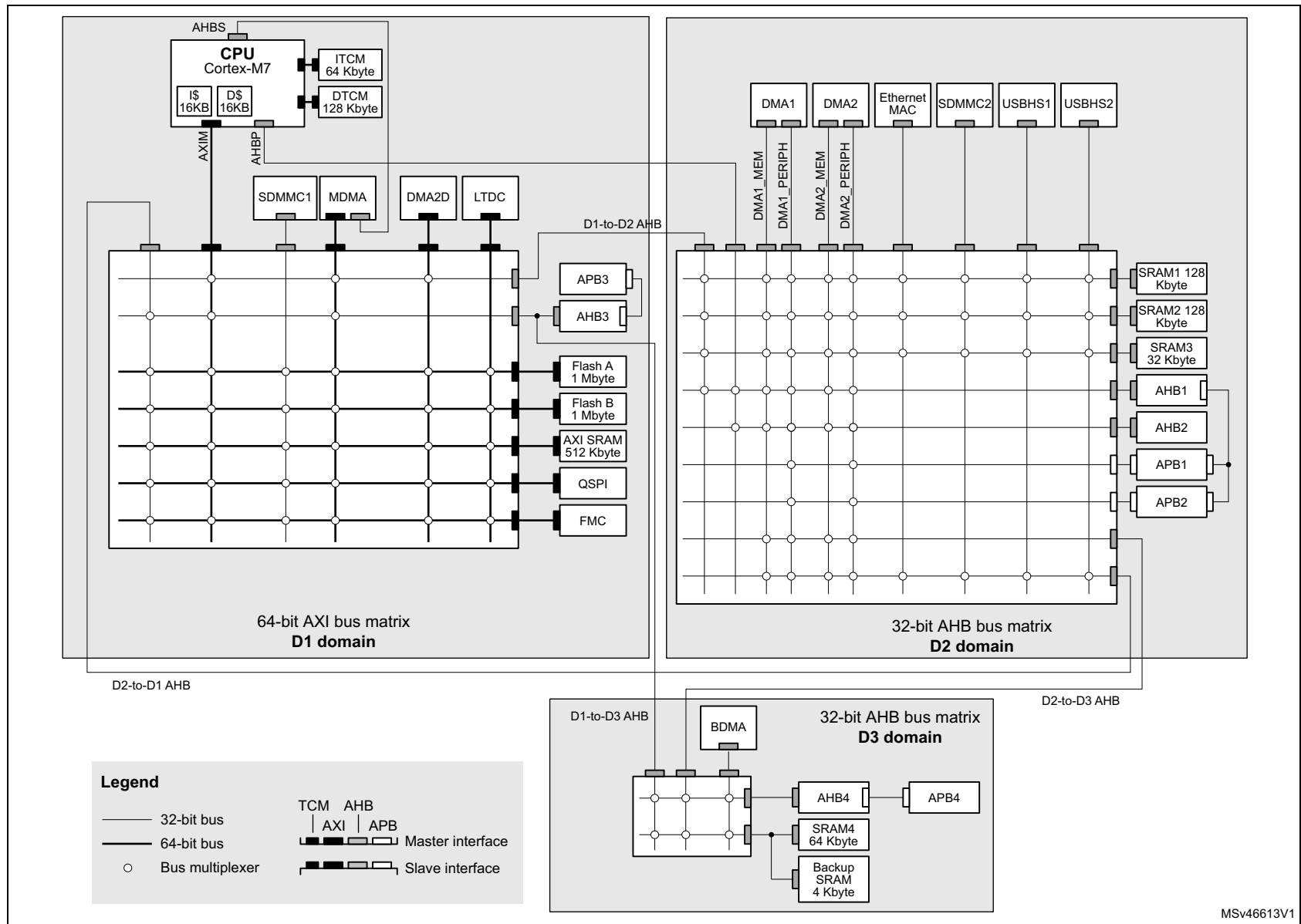
During power-up and power-down phases, the following power sequence requirements must be respected (see [Figure 2](#)):

- When V_{DD} is below 1 V, other power supplies (V_{DDA} , $V_{DD33USB}$, $V_{DD50USB}$) must remain below $V_{DD} + 300$ mV.
- When V_{DD} is above 1 V, all power supplies are independent.

During the power-down phase, V_{DD} can temporarily become lower than other supplies only if the energy provided to the microcontroller remains below 1 mJ. This allows external decoupling capacitors to be discharged with different time constants during the power-down transient phase.



Figure 3. STM32H753xl bus matrix



3.31 Inter-integrated circuit interface (I2C)

STM32H753xI devices embed four I²C interfaces.

The I²C bus interface handles communications between the microcontroller and the serial I²C bus. It controls all I²C bus-specific sequencing, protocol, arbitration and timing.

The I2C peripheral supports:

- I²C-bus specification and user manual rev. 5 compatibility:
 - Slave and Master modes, multimaster capability
 - Standard-mode (Sm), with a bitrate up to 100 kbit/s
 - Fast-mode (Fm), with a bitrate up to 400 kbit/s
 - Fast-mode Plus (Fm+), with a bitrate up to 1 Mbit/s and 20 mA output drive I/Os
 - 7-bit and 10-bit addressing mode, multiple 7-bit slave addresses
 - Programmable setup and hold times
 - Optional clock stretching
- System Management Bus (SMBus) specification rev 2.0 compatibility:
 - Hardware PEC (Packet Error Checking) generation and verification with ACK control
 - Address resolution protocol (ARP) support
 - SMBus alert
- Power System Management Protocol (PMBus™) specification rev 1.1 compatibility
- Independent clock: a choice of independent clock sources allowing the I2C communication speed to be independent from the PCLK reprogramming.
- Wakeup from Stop mode on address match
- Programmable analog and digital noise filters
- 1-byte buffer with DMA capability

3.32 Universal synchronous/asynchronous receiver transmitter (USART)

STM32H753xI devices have four embedded universal synchronous receiver transmitters (USART1, USART2, USART3 and USART6) and four universal asynchronous receiver transmitters (UART4, UART5, UART7 and UART8). Refer to [Table 6](#) for a summary of USARTx and UARTx features.

These interfaces provide asynchronous communication, IrDA SIR ENDEC support, multiprocessor communication mode, single-wire Half-duplex communication mode and have LIN Master/Slave capability. They provide hardware management of the CTS and RTS signals, and RS485 Driver Enable. They are able to communicate at speeds of up to 12.5 Mbit/s.

USART1, USART2, USART3 and USART6 also provide Smartcard mode (ISO 7816 compliant) and SPI-like communication capability.

The USARTs embed a Transmit FIFO (TXFIFO) and a Receive FIFO (RXFIFO). FIFO mode is enabled by software and is disabled by default.

3.36 SPDIFRX Receiver Interface (SPDIFRX)

The SPDIFRX peripheral is designed to receive an S/PDIF flow compliant with IEC-60958 and IEC-61937. These standards support simple stereo streams up to high sample rate, and compressed multi-channel surround sound, such as those defined by Dolby or DTS (up to 5.1).

The main SPDIFRX features are the following:

- Up to 4 inputs available
- Automatic symbol rate detection
- Maximum symbol rate: 12.288 MHz
- Stereo stream from 32 to 192 kHz supported
- Supports Audio IEC-60958 and IEC-61937, consumer applications
- Parity bit management
- Communication using DMA for audio samples
- Communication using DMA for control and user channel information
- Interrupt capabilities

The SPDIFRX receiver provides all the necessary features to detect the symbol rate, and decode the incoming data stream. The user can select the wanted SPDIF input, and when a valid signal will be available, the SPDIFRX will re-sample the incoming signal, decode the Manchester stream, recognize frames, sub-frames and blocks elements. It delivers to the CPU decoded data, and associated status flags.

The SPDIFRX also offers a signal named `spdif_frame_sync`, which toggles at the S/PDIF sub-frame rate that will be used to compute the exact sample rate for clock drift algorithms.

3.37 Single wire protocol master interface (SWPMI)

The Single wire protocol master interface (SWPMI) is the master interface corresponding to the Contactless Frontend (CLF) defined in the ETSI TS 102 613 technical specification. The main features are:

- Full-duplex communication mode
- automatic SWP bus state management (active, suspend, resume)
- configurable bitrate up to 2 Mbit/s
- automatic SOF, EOF and CRC handling

SWPMI can be served by the DMA controller.

Table 8. STM32H753xI pin/ball definition (continued)

Pin/ball name								Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	TFBGA100	LQFP144	UFBGA169	UFBGA176+25	LQFP176	LQFP208	TFBGA240 +25						
31	K3	43	J6	R3	53	56	R5	PA7	I/O	TT_a	-	TIM1_CH1N, TIM3_CH2, TIM8_CH1N, SPI1_MOSI/I2S1_SDO, SPI6_MOSI, TIM14_CH1, ETH_MII_RX_DV/ETH_R MII_CRS_DV, FMC_SDNWE, EVENTOUT	ADC12_INN3, ADC12_INP7, OPAMP1_VINM
32	G4	44	K6	N5	54	57	T4	PC4	I/O	TT_a	-	DFSDM_CKIN2, I2S1_MCK, SPDIFRX_IN2, ETH_MII_RXD0/ETH_R MII_RXD0, FMC_SDNE0, EVENTOUT	ADC12_INP4, OPAMP1_ VOUT, COMP_1_INM
33	H4	45	N5	P5	55	58	U4	PC5	I/O	TT_a	-	SAI1_D3, DFSDM_DATIN2, SPDIFRX_IN3, SAI4_D3, ETH_MII_RXD1/ETH_R MII_RXD1, FMC_SDCKE0, COMP_1_OUT, EVENTOUT	ADC12_INN4, ADC12_INP8, OPAMP1_ VINM
-	-	-	N4	-	-	59	G13	VDD	S	-	-	-	-
-	-	-	H12	J9	-	60	G16	VSS	S	-	-	-	-
34	J4	46	M5	R5	56	61	U5	PB0	I/O	FT_a	-	TIM1_CH2N, TIM3_CH3, TIM8_CH2N, DFSDM_CKOUT, UART4_CTS, LCD_R3, OTG_HS_ULPI_D1, ETH_MII_RXD2, LCD_G1, EVENTOUT	ADC12_INN5, ADC12_INP9, OPAMP1_VINP, COMP_1_INP
35	K4	47	L5	R4	57	62	T5	PB1	I/O	TT_u	-	TIM1_CH3N, TIM3_CH4, TIM8_CH3N, DFSDM_DATIN1, LCD_R6, OTG_HS_ULPI_D2, ETH_MII_RXD3, LCD_G0, EVENTOUT	ADC12_INP5, COMP_1_INM
36	G5	48	L6	M6	58	63	R6	PB2	I/O	FT_ ha	-	SAI1_D1, DFSDM_CKIN1, SAI1_SD_A, SPI3_MOSI/I2S3_SDO, SAI4_SD_A, QUADSPI_CLK, SAI4_D1, EVENTOUT	COMP_1_INP, RTC_OUT

Table 8. STM32H753xl pin/ball definition (continued)

Pin/ball name								Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	TFBGA100	LQFP144	UFBGA169	UFBGA176+25	LQFP176	LQFP208	TFBGA240 +25						
-	-	-	-	E12	128	151	D16	PH13	I/O	FT_h	-	TIM8_CH1N, UART4_TX, FDCAN1_TX, FMC_D21, LCD_G2, EVENTOUT	-
-	-	-	-	E13	129	152	B17	PH14	I/O	FT_h	-	TIM8_CH2N, UART4_RX, FDCAN1_RX, FMC_D22, DCMI_D4, LCD_G3, EVENTOUT	-
-	-	-	-	D13	130	153	B16	PH15	I/O	FT_h	-	TIM8_CH3N, FDCAN1_TXFD_MODE, FMC_D23, DCMI_D11, LCD_G4, EVENTOUT	-
-	-	-	A13	E14	131	154	A16	PI0	I/O	FT_h	-	TIM5_CH4, SPI2_NSS/I2S2_WS, FDCAN1_RXFD_MODE, FMC_D24, DCMI_D13, LCD_G5, EVENTOUT	-
-	-	-	-	G9	-	-	-	VSS	S	-	-	-	-
-	-	-	B13	D14	132	155	A15	PI1	I/O	FT_h	-	TIM8_BKIN2, SPI2_SCK/I2S2_CK, TIM8_BKIN2_COMP12, FMC_D25, DCMI_D8, LCD_G6, EVENTOUT	-
-	-	-	A6	C14	133	156	B15	PI2	I/O	FT_h	-	TIM8_CH4, SPI2_MISO/I2S2_SDI, FMC_D26, DCMI_D9, LCD_G7, EVENTOUT	-
-	-	-	B7	C13	134	157	C14	PI3	I/O	FT_h	-	TIM8_ETR, SPI2_MOSI/I2S2_SDO, FMC_D27, DCMI_D10, EVENTOUT	-
-	-	-	-	D9	135	-	-	VSS	S	-	-	-	-
-	-	-	-	C9	136	158	-	VDD	S	-	-	-	-
76	A9	109	B12	A14	137	159	B14	PA14 (JTCK/SW CLK)	I/O	FT	-	JTCK-SWCLK, EVENTOUT	-
77	A8	110	C11	A13	138	160	A14	PA15 (JTDI)	I/O	FT	-	JTDI, TIM2_CH1/TIM2_ETR, HRTIM_FLT1, HDMI_CEC, SPI1_NSS/I2S1_WS, SPI3_NSS/I2S3_WS, SPI6_NSS, UART4_RTS, UART7_TX, EVENTOUT	-

Table 11. Port C alternate functions

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	TIM1/2/16/17/LPTIM1/HRTIM1	SAI1/TIM3/4/5/12/HRTIM1	LPUART/TIM8/LPTIM2/3/4/5/HRTIM1/DFSDM	I2C1/2/3/4/USART1/TIM15/LPTIM2/DFSDM/CEC	SPI1/2/3/4/5/6/CEC	SPI2/3/SAI1/3/I2C4/UART4/DFSDM	SPI2/3/6/USART1/2/3/6/UART7/SDMMC1	SPI6/SAI2/4/UART4/5/8/LPUART/SDMMC1/SPDIFRX	SAI4/FDCAN1/2/TIM13/14/QUADSPI/FMC/SDMMC2/LCD/SPDIFRX	SAI2/4/TIM8/QUADSPI/SDMMC2/OTG1_HS/OTG2_FS/LCD	I2C4/UART7/SWPMI1/TIM1/8/DFSDM/SDMMC2/MDIOS/ETH	TIM1/8/FMC/SDMMC1/MDIOS/OTG1_FS/LCD	TIM1/DCMI/LCD/COMP	UART5/LCD	SYS
Port C	PC0	-	-	-	DFSDM_CKIN0	-	-	DFSDM_DATIN4	-	SAI2_FS_B	-	OTG_HS_ULPI_STP	-	FMC_SDNWE	-	LCD_R5	EVENT-OUT
	PC1	TRACED0	-	SAI1_D1	DFSDM_DATIN0	DFSDM_CKIN4	SPI2_MOSI/I2S2_SDO	SAI1_SD_A	-	SAI4_SD_A	SDMMC2_CK	SAI4_D1	ETH_MDC	MDIOS_MDC	-	-	EVENT-OUT
	PC2	-	-	-	DFSDM_CKIN1	-	SPI2_MISO/I2S2_SDI	DFSDM_CK_OUT	-	-	-	OTG_HS_ULPI_DIR	ETH_MII_TXD2	FMC_SDNE0	-	-	EVENT-OUT
	PC3	-	-	-	DFSDM_DATIN1	-	SPI2_MOSI/I2S2_SDO	-	-	-	-	OTG_HS_ULPI_NXT	ETH_MII_TX_CLK	FMC_SDCKE0	-	-	EVENT-OUT
	PC4	-	-	-	DFSDM_CKIN2	-	I2S1_MCK	-	-	-	SPDIFRX_IN2	-	ETH_MII_RXD0/ETH_RMII_RXD0	FMC_SDNE0	-	-	EVENT-OUT
	PC5	-	-	SAI1_D3	DFSDM_DATIN2	-	-	-	-	SPDIFRX_IN3	SAI4_D3	ETH_MII_RXD1/ETH_RMII_RXD1	FMC_SDCKE0	COMP_1_OUT	-	-	EVENT-OUT
	PC6	-	HRTIM_CHA1	TIM3_CH1	TIM8_CH1	DFSDM_CKIN3	I2S2_MCK	-	USART6_TX	SDMMC1_D0DIR	FMC_NWAIT	SDMMC2_D6	-	SDMMC1_D6	DCMI_D0	LCD_HSYNC	EVENT-OUT
	PC7	TRGIO	HRTIM_CHA2	TIM3_CH2	TIM8_CH2	DFSDM_DATIN3	-	I2S3_MCK	USART6_RX	SDMMC1_D123DIR	FMC_NE1	SDMMC2_D7	SWPMI_TX	SDMMC1_D7	DCMI_D1	LCD_G6	EVENT-OUT
	PC8	TRACED1	HRTIM_CHB1	TIM3_CH3	TIM8_CH3	-	-	-	USART6_CK	UART5_RTS	FMC_NE2/FMC_NCE	-	SWPMI_RX	SDMMC1_D0	DCMI_D2	-	EVENT-OUT
	PC9	MCO2	-	TIM3_CH4	TIM8_CH4	I2C3_SDA	I2S_CKIN	-	-	UART5_CTS	QUADSPI_BK1_IO0	LCD_G3	SWPMI_SUSPEND	SDMMC1_D1	DCMI_D3	LCD_B2	EVENT-OUT
	PC10	-	-	HRTIM_EEV1	DFSDM_CKIN5	-	-	SPI3_SCK/I2S3_CK	USART3_TX	UART4_TX	QUADSPI_BK1_IO1	-	-	SDMMC1_D2	DCMI_D8	LCD_R2	EVENT-OUT
	PC11	-	-	HRTIM_FLT2	DFSDM_DATIN5	-	-	SPI3_MISO/I2S3_SDI	USART3_RX	UART4_RX	QUADSPI_BK2_NCS	-	-	SDMMC1_D3	DCMI_D4	-	EVENT-OUT
	PC12	TRACED3	-	HRTIM_EEV2	-	-	-	SPI3_MOSI/I2S3_SDO	USART3_CK	UART5_TX	-	-	-	SDMMC1_CK	DCMI_D9	-	EVENT-OUT
	PC13	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT-OUT

Table 11. Port C alternate functions (continued)

Port	AF0		AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
	SYS		TIM1/2/16/17/LPTIM1/HRTIM1	SAI1/TIM3/4/5/12/HRTIM1	LPUART/TIM8/LPTIM2/3/4/5/HRTIM1/DFSDM	I2C1/2/3/4/USART1/TIM15/LPTIM2/DFSDM/CEC	SP11/2/3/4/5/6/CEC	SPI2/3/SAI1/3/I2C4/UART4/DFSDM	SPI2/3/6/USART1/2/3/6/UART7/SDMMC1	SPI6/SAI2/4/UART4/5/8/LPUART/SDMMC1/SPDIFRX	SAI4/FDCAN1/2/TIM13/14/QUADSPI/FMC/SDMMC2/LCD/SPDIFRX	SAI2/4/TIM8/QUADSPI/SDMMC2/OTG1_HS/OTG2_FS/LCD	I2C4/UART7/SWPMI1/TIM1/8/DFSDM/SDMMC2/MDIOS/ETH	TIM1/8/FMC/SDMMC1/MDIOS/OTG1_FS/LCD	TIM1/DCMI/LCD/COMP	UART5/LCD	SYS
Port C	PC14	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT-OUT
	PC15	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT-OUT



Table 13. Port E alternate functions

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	TIM1/2/16/17/LPTIM1/HRTIM1	SAI1/TIM3/4/5/12/HRTIM1	LPUART/TIM8/LPTIM2/3/4/5/HRTIM1/DFSDM	I2C1/2/3/4/USART1/TIM15/LPTIM2/DFSDM/CEC	SPI1/2/3/4/5/6/CEC	SPI2/3/SAI1/3/I2C4/UART4/DFSDM	SPI2/3/6/USART1/2/3/6/UART7/SDMMC1	SPI6/SAI2/4/UART4/5/8/LPUART/SDMMC1/SPDIFRX	SAI4/FDCAN1/2/TIM13/14/QUADSPI/FMC/SDMMC2/LCD/SPDIFRX	SAI2/4/TIM8/QUADSPI/SDMMC2/OTG1_HS/OTG2_FS/LCD	I2C4/UART7/SWPMI1/TIM1/8/DFSDM/SDMMC2/MDIOS/ETH	TIM1/8/FMC/SDMMC1/MDIOS/OTG1_FS/LCD	TIM1/DCMI/LCD/COMP	UART5/LCD	SYS
Port E	PE0	-	LPTIM1_ETR	TIM4_ETR	HRTIM_SCIN	LPTIM2_ETR	-	-	-	UART8_RX	FDCAN1_RXFD_MODE	SAI2_MCK_A	-	FMC_NBL0	DCMI_D2	-	EVENT-OUT
	PE1	-	LPTIM1_IN2	-	HRTIM_SCOUT	-	-	-	-	UART8_TX	FDCAN1_TXFD_MODE	-	-	FMC_NBL1	DCMI_D3	-	EVENT-OUT
	PE2	TRACE_CLK	-	SAI1_CK1	-	-	SPI4_SCK	SAI1_MCLK_A	-	SAI4_MCLK_A	QUADSPI_BK1_IO2	SAI4_CK1	ETH_MIL_TXD3	FMC_A23	-	-	EVENT-OUT
	PE3	TRACED0	-	-	-	TIM15_BKIN	-	SAI1_SD_B	-	SAI4_SD_B	-	-	-	FMC_A19	-	-	EVENT-OUT
	PE4	TRACED1	-	SAI1_D2	DFSDM_DATIN3	TIM15_CH1N	SPI4_NSS	SAI1_FS_A	-	SAI4_FS_A	-	SAI4_D2	-	FMC_A20	DCMI_D4	LCD_B0	EVENT-OUT
	PE5	TRACED2	-	SAI1_CK2	DFSDM_CKIN3	TIM15_CH1	SPI4_MISO	SAI1_SCK_A	-	SAI4_SCK_A	-	SAI4_CK2	-	FMC_A21	DCMI_D6	LCD_G0	EVENT-OUT
	PE6	TRACED3	TIM1_BKIN2	SAI1_D1	-	TIM15_CH2	SPI4_MOSI	SAI1_SD_A	-	SAI4_SD_A	SAI4_D1	SAI2_MCK_B	TIM1_BKIN2_COMP12	FMC_A22	DCMI_D7	LCD_G1	EVENT-OUT
	PE7	-	TIM1_ETR	-	DFSDM_DATIN2	-	-	-	UART7_RX	-	-	QUADSPI_BK2_IO0	-	FMC_D4/FMC_DA4	-	-	EVENT-OUT
	PE8	-	TIM1_CH1N	-	DFSDM_CKIN2	-	-	-	UART7_TX	-	-	QUADSPI_BK2_IO1	-	FMC_D5/FMC_DA5	COMP_2_OUT	-	EVENT-OUT
	PE9	-	TIM1_CH1	-	DFSDM_CKOUT	-	-	-	UART7_RTS	-	-	QUADSPI_BK2_IO2	-	FMC_D6/FMC_DA6	-	-	EVENT-OUT
	PE10	-	TIM1_CH2N	-	DFSDM_DATIN4	-	-	-	UART7_CTS	-	-	QUADSPI_BK2_IO3	-	FMC_D7/FMC_DA7	-	-	EVENT-OUT
	PE11	-	TIM1_CH2	-	DFSDM_CKIN4	-	SPI4_NSS	-	-	-	-	SAI2_SD_B	-	FMC_D8/FMC_DA8	-	LCD_G3	EVENT-OUT
	PE12	-	TIM1_CH3N	-	DFSDM_DATIN5	-	SPI4_SCK	-	-	-	-	SAI2_SCK_B	-	FMC_D9/FMC_DA9	COMP_1_OUT	LCD_B4	EVENT-OUT
	PE13	-	TIM1_CH3	-	DFSDM_CKIN5	-	SPI4_MISO	-	-	-	-	SAI2_FS_B	-	FMC_D10/FMC_DA10	COMP_2_OUT	LCD_DE	EVENT-OUT
	PE14	-	TIM1_CH4	-	-	-	SPI4_MOSI	-	-	-	-	SAI2_MCK_B	-	FMC_D11/FMC_DA11	-	LCD_CLK	EVENT-OUT
	PE15	-	TIM1_BKIN	-	-	-	HDMI_TIM1_BKIN	-	-	-	-	-	-	FMC_D12/FMC_DA12	TIM1_BKIN_COMP12	LCD_R7	EVENT-OUT

Table 27. Embedded reference voltage (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{REFINT_DIV1}	1/4 reference voltage	-	-	25	-	% V _{REFINT}
V _{REFINT_DIV2}	1/2 reference voltage	-	-	50	-	
V _{REFINT_DIV3}	3/4 reference voltage	-	-	75	-	

1. The shortest sampling time for the application can be determined by multiple iterations.
2. Guaranteed by design.

Table 28. Internal reference voltage calibration values

Symbol	Parameter	Memory address
V _{REFIN_CAL}	Raw data acquired at temperature of 30 °C, V _{DDA} = 3.3 V	1FF1E860 - 1FF1E861

6.3.6 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.

The current consumption is measured as described in [Figure 15: Current consumption measurement scheme](#).

All the run-mode current consumption measurements given in this section are performed with a CoreMark code.

Typical and maximum current consumption

The MCU is placed under the following conditions:

- All I/O pins are in analog input mode.
- All peripherals are disabled except when explicitly mentioned.
- The Flash memory access time is adjusted with the minimum wait states number, depending on the f_{ACLK} frequency (refer to the table “Number of wait states according to CPU clock (f_{ICC_CCK}) frequency and V_{CORE} range” available in the reference manual).
- When the peripherals are enabled, the AHB clock frequency is the CPU frequency divided by 2 and the APB clock frequency is AHB clock frequency divided by 2.

The parameters given in [Table 29](#) to [Table 37](#) are derived from tests performed under ambient temperature and supply voltage conditions summarized in [Table 23: General operating conditions](#).

Table 35. Typical and maximum current consumption in Stop mode, regulator ON

Symbol	Parameter	Conditions		Typ	Max ⁽¹⁾				unit
					T _J = 25°C	T _J = 85°C	T _J = 105°C	T _J = 125°C	
I _{DD(Stop)}	D1Stop, D2Stop, D3Stop	Flash memory in low-power mode, no IWDG	SVOS5	1.4	7.2 ⁽²⁾	49	75 ⁽²⁾	140	mA
			SVOS4	1.95	11	66	110	200	
			SVOS3	2.85	16 ⁽²⁾	91	150 ⁽²⁾	240	
		Flash memory ON, no IWDG	SVOS5	1.65	7.2	49	75	140	
			SVOS4	2.2	11	66	110	180	
			SVOS3	3.15	16	91	150	300	
	D1Stop, D2Standby, D3Stop	Flash memory OFF, no IWDG	SVOS5	0.99	5.1	35	60	97	
			SVOS4	1.4	7.5	47	79	130	
			SVOS3	2.05	12	64	110	170	
		Flash memory ON, no IWDG	SVOS5	1.25	5.5	35	61	98	
			SVOS4	1.65	7.8	47	80	130	
			SVOS3	2.3	12	65	110	170	
	D1Standby, D2Stop, D3Stop	Flash OFF, no IWDG	SVOS5	0.57	3	21	36	57	
			SVOS4	0.805	4.5	27	47	74	
			SVOS3	1.2	6.7	37	63	99	
	D1Standby, D2Standby, D3Stop		SVOS5	0.17	1.1 ⁽²⁾	8	13 ⁽²⁾	20	
			SVOS4	0.245	1.5	11	17	26	
			SVOS3	0.405	2.4 ⁽²⁾	15	23 ⁽²⁾	35	

1. Guaranteed by characterization results.

2. Guaranteed by test in production.

Table 36. Typical and maximum current consumption in Standby mode

Symbol	Parameter	Conditions		Typ ⁽³⁾				Max (3 V) ⁽¹⁾				Unit
		Backup SRAM	RTC & LSE	1.62 V	2.4 V	3 V	3.3 V	T _J = 25°C	T _J = 85°C	T _J = 105°C	T _J = 125°C	
I _{DD} (Standby)	Supply current in Standby mode	OFF	OFF	1.8	1.9	1.95	2.05	4 ⁽²⁾	18 ⁽³⁾	40 ⁽²⁾	90 ⁽³⁾	μA
		ON	OFF	3.4	3.4	3.5	3.7	8.2 ⁽³⁾	47 ⁽³⁾	83 ⁽³⁾	141 ⁽³⁾	
		OFF	ON	2.4	3.5	3.86	4.12	-	-	-	-	
		ON	ON	3.95	5.1	5.46	5.97	-	-	-	-	

1. The maximum current consumption values are given for PDR OFF (internal reset OFF). When the PDR is OFF (internal reset OFF), the current consumption is reduced by 1.2 μA compared to PDR ON.

2. Guaranteed by test in production.

3. Guaranteed by characterization results.

Static latchup

Two complementary static tests are required on six parts to assess the latchup performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with JESD78 IC latchup standard.

Table 57. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latchup class	$T_A = +25\text{ }^{\circ}\text{C}$ conforming to JESD78	II level A

6.3.14 I/O current injection characteristics

As a general rule, a current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard, 3.3 V-capable I/O pins) should be avoided during the normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when an abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during the device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (higher than 5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of $-5\text{ }\mu\text{A}/+0\text{ }\mu\text{A}$ range), or other functional failure (for example reset, oscillator frequency deviation).

The following tables are the compilation of the SIC1/SIC2 and functional ESD results.

Negative induced A negative induced leakage current is caused by negative injection and positive induced leakage current by positive injection.

Table 58. I/O current injection susceptibility⁽¹⁾

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I_{INJ}	PA7, PC5, PG1, PB14, PJ7, PA11, PA12, PA13, PA14, PA15, PJ12, PB4	5	0	mA
	PA2, PH2, PH3, PE8, PA6, PA7, PC4, PE7, PE10, PE11	0	NA	
	PA0, PA_C, PA1, PA1_C, PC2, PC2_C, PC3, PC3_C, PA4, PA5, PH4, PH5, BOOT0	0	0	
	All other I/Os	5	NA	

1. Guaranteed by characterization.

Table 61. Output timing characteristics (HSLV OFF)⁽¹⁾ (continued)

Speed	Symbol	Parameter	conditions	Min	Max	Unit
10	$F_{\max}^{(2)}$	Maximum frequency	C=50 pF, 2.7 V ≤ V _{DD} ≤ 3.6 V ⁽⁴⁾	-	85	MHz
			C=50 pF, 1.62 V ≤ V _{DD} ≤ 2.7 V ⁽⁴⁾	-	35	
			C=30 pF, 2.7 V ≤ V _{DD} ≤ 3.6 V ⁽⁴⁾	-	110	
			C=30 pF, 1.62 V ≤ V _{DD} ≤ 2.7 V ⁽⁴⁾	-	40	
			C=10 pF, 2.7 V ≤ V _{DD} ≤ 3.6 V ⁽⁴⁾	-	166	
			C=10 pF, 1.62 V ≤ V _{DD} ≤ 2.7 V ⁽⁴⁾	-	100	
	$t_r/t_f^{(3)}$	Output high to low level fall time and output low to high level rise time	C=50 pF, 2.7 V ≤ V _{DD} ≤ 3.6 V ⁽⁴⁾	-	3.8	ns
			C=50 pF, 1.62 V ≤ V _{DD} ≤ 2.7 V ⁽⁴⁾	-	6.9	
			C=30 pF, 2.7 V ≤ V _{DD} ≤ 3.6 V ⁽⁴⁾	-	2.8	
			C=30 pF, 1.62 V ≤ V _{DD} ≤ 2.7 V ⁽⁴⁾	-	5.2	
			C=10 pF, 2.7 V ≤ V _{DD} ≤ 3.6 V ⁽⁴⁾	-	1.8	
			C=10 pF, 1.62 V ≤ V _{DD} ≤ 2.7 V ⁽⁴⁾	-	3.3	
11	$F_{\max}^{(2)}$	Maximum frequency	C=50 pF, 2.7 V ≤ V _{DD} ≤ 3.6 V ⁽⁴⁾	-	100	MHz
			C=50 pF, 1.62 V ≤ V _{DD} ≤ 2.7 V ⁽⁴⁾	-	50	
			C=30 pF, 2.7 V ≤ V _{DD} ≤ 3.6 V ⁽⁴⁾	-	133	
			C=30 pF, 1.62 V ≤ V _{DD} ≤ 2.7 V ⁽⁴⁾	-	66	
			C=10 pF, 2.7 V ≤ V _{DD} ≤ 3.6 V ⁽⁴⁾	-	220	
			C=10 pF, 1.62 V ≤ V _{DD} ≤ 2.7 V ⁽⁴⁾	-	85	
	$t_r/t_f^{(3)}$	Output high to low level fall time and output low to high level rise time	C=50 pF, 2.7 V ≤ V _{DD} ≤ 3.6 V ⁽⁴⁾	-	3.3	ns
			C=50 pF, 1.62 V ≤ V _{DD} ≤ 2.7 V ⁽⁴⁾	-	6.6	
			C=30 pF, 2.7 V ≤ V _{DD} ≤ 3.6 V ⁽⁴⁾	-	2.4	
			C=30 pF, 1.62 V ≤ V _{DD} ≤ 2.7 V ⁽⁴⁾	-	4.5	
			C=10 pF, 2.7 V ≤ V _{DD} ≤ 3.6 V ⁽⁴⁾	-	1.5	
			C=10 pF, 1.62 V ≤ V _{DD} ≤ 2.7 V ⁽⁴⁾	-	2.7	

1. Guaranteed by design.
2. The maximum frequency is defined with the following conditions:
 $(t_r + t_f) \leq 2/3 T$
Skew ≤ 1/20 T
45% < Duty cycle < 55%
3. The fall and rise times are defined between 90% and 10% and between 10% and 90% of the output waveform, respectively.
4. Compensation system enabled.

6.3.16 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R_{PU} (see [Table 59: I/O static characteristics](#)).

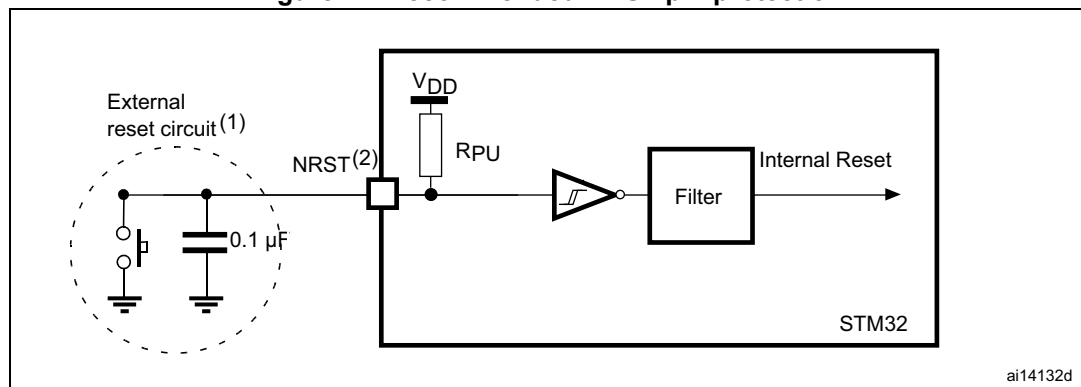
Unless otherwise specified, the parameters given in [Table 63](#) are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in [Table 23: General operating conditions](#).

Table 63. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{PU}^{(2)}$	Weak pull-up equivalent resistor ⁽¹⁾	$V_{IN} = V_{SS}$	30	40	50	k Ω
$V_{F(NRST)}^{(2)}$	NRST Input filtered pulse	$1.71\text{ V} < V_{DD} < 3.6\text{ V}$	-	-	50	ns
$V_{NF(NRST)}^{(2)}$	NRST Input not filtered pulse	$1.71\text{ V} < V_{DD} < 3.6\text{ V}$	300	-	-	
		$1.62\text{ V} < V_{DD} < 3.6\text{ V}$	1000	-	-	

1. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance must be minimum (~10% order).
2. Guaranteed by design.

Figure 22. Recommended NRST pin protection



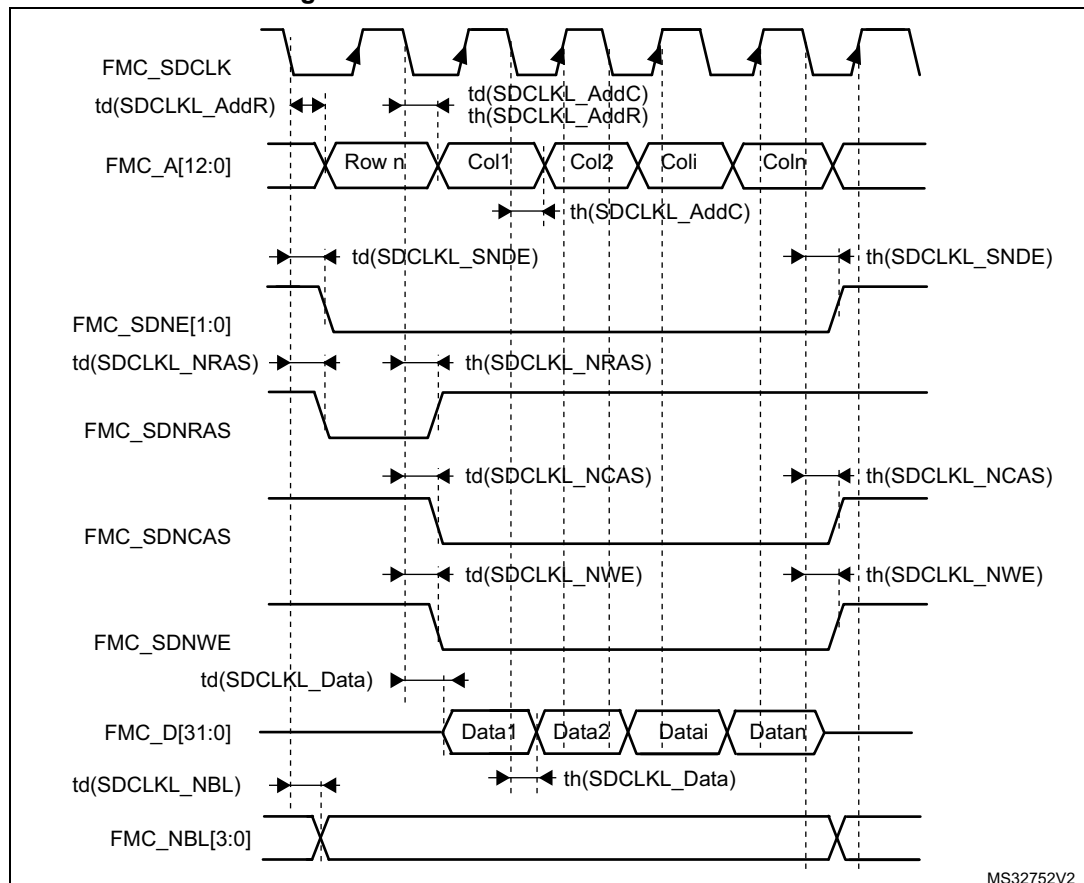
1. The reset network protects the device against parasitic resets.
2. The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in [Table 63](#). Otherwise the reset is not taken into account by the device.

Table 79. LPSDR SDRAM read timings⁽¹⁾

Symbol	Parameter	Min	Max	Unit
$t_{W(SDCLK)}$	FMC_SDCLK period	$2T_{fmc_ker_ck} - 1$	$2T_{fmc_ker_ck} + 0.5$	ns
$t_{su(SDCLKH_Data)}$	Data input setup time	2	-	
$t_{h(SDCLKH_Data)}$	Data input hold time	1.5	-	
$t_d(SDCLKL_Add)$	Address valid time	-	2.5	
$t_d(SDCLKL_SDNE)$	Chip select valid time	-	2.5	
$t_h(SDCLKL_SDNE)$	Chip select hold time	0	-	
$t_d(SDCLKL_SDNRAS)$	SDNRAS valid time	-	0.5	
$t_h(SDCLKL_SDNRAS)$	SDNRAS hold time	0	-	
$t_d(SDCLKL_SDNCAS)$	SDNCAS valid time	-	1.5	
$t_h(SDCLKL_SDNCAS)$	SDNCAS hold time	0	-	

1. Guaranteed by characterization results.

Figure 36. SDRAM write access waveforms



6.3.26 Comparator characteristics

Table 95. COMP characteristics⁽¹⁾

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V _{DDA}	Analog supply voltage	-		1.62	3.3	3.6	V
V _{IN}	Comparator input voltage range	-		0	-	V _{DDA}	
V _{BG} ⁽²⁾	Scaler input voltage	-		Refer to V _{REFINT}			
V _{SC}	Scaler offset voltage	-		-	±5	±10	
I _{DDA(SCALER)}	Scaler static consumption from V _{DDA}	BRG_EN=0 (bridge disable)		-	0.2	0.3	µA
		BRG_EN=1 (bridge enable)		-	0.8	1	
t _{START_SCALER}	Scaler startup time	-		-	140	250	µs
t _{START}	Comparator startup time to reach propagation delay specification	High-speed mode		-	2	5	µs
		Medium mode		-	5	20	
		Ultra-low-power mode		-	15	80	
t _D	Propagation delay for 200 mV step with 100 mV overdrive	High-speed mode		-	50	80	ns
		Medium mode		-	0.5	1.2	µs
		Ultra-low-power mode		-	2.5	7	
	Propagation delay for step > 200 mV with 100 mV overdrive only on positive inputs	High-speed mode		-	50	120	ns
		Medium mode		-	0.5	1.2	µs
		Ultra-low-power mode		-	2.5	7	
V _{offset}	Comparator offset error	Full common mode range		-	±5	±20	mV
V _{hys}	Comparator hysteresis	No hysteresis		-	0	-	mV
		Low hysteresis		-	10	-	
		Medium hysteresis		-	20	-	
		High hysteresis		-	30	-	
I _{DDA(COMP)}	Comparator consumption from V _{DDA}	Ultra-low-power mode	Static	-	400	600	nA
			With 50 kHz ±100 mV overdrive square signal	-	800	-	
		Medium mode	Static	-	5	7	µA
			With 50 kHz ±100 mV overdrive square signal	-	6	-	
		High-speed mode	Static	-	70	100	
			With 50 kHz ±100 mV overdrive square signal	-	75	-	

1. Guaranteed by design, unless otherwise specified.

2. Refer to [Table 27: Embedded reference voltage](#).

6.3.30 LCD-TFT controller (LTDC) characteristics

Unless otherwise specified, the parameters given in [Table 99](#) for LCD-TFT are derived from tests performed under the ambient temperature, $f_{\text{rcc_c_ck}}$ frequency and V_{DD} supply voltage summarized in [Table 23: General operating conditions](#), with the following configuration:

- LCD_CLK polarity: high
- LCD_DE polarity: low
- LCD_VSYNC and LCD_HSYNC polarity: high
- Pixel formats: 24 bits
- Output speed is set to OSPEEDRy[1:0] = 11
- Capacitive load C=30 pF
- Measurement points are done at CMOS levels: $0.5V_{\text{DD}}$
- I/O compensation cell enabled

Table 99. LTDC characteristics ⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
f_{CLK}	LTDC clock output frequency	$2.7\text{ V} < V_{\text{DD}} < 3.6\text{ V}$, 20 pF	-	150	MHz
		$2.7\text{ V} < V_{\text{DD}} < 3.6\text{ V}$	-	133	
		$1.62\text{ V} < V_{\text{DD}} < 3.6\text{ V}$	-	90	
D_{CLK}	LTDC clock output duty cycle	-	45	55	%
$t_{\text{w}}(\text{CLKH})$, $t_{\text{w}}(\text{CLKL})$	Clock High time, low time		$t_{\text{w}}(\text{CLK})/2-0.5$	$t_{\text{w}}(\text{CLK})/2+0.5$	ns
$t_{\text{v}}(\text{DATA})$	Data output valid time		-	0.5	
$t_{\text{h}}(\text{DATA})$	Data output hold time		0	-	
$t_{\text{v}}(\text{HSYNC})$, $t_{\text{v}}(\text{VSYNC})$, $t_{\text{v}}(\text{DE})$	HSYNC/VSYNC/DE output valid time		-	0.5	
$t_{\text{h}}(\text{HSYNC})$, $t_{\text{h}}(\text{VSYNC})$, $t_{\text{h}}(\text{DE})$	HSYNC/VSYNC/DE output hold time		0.5	-	

1. Guaranteed by characterization results.

Figure 53. SAI master timing waveforms

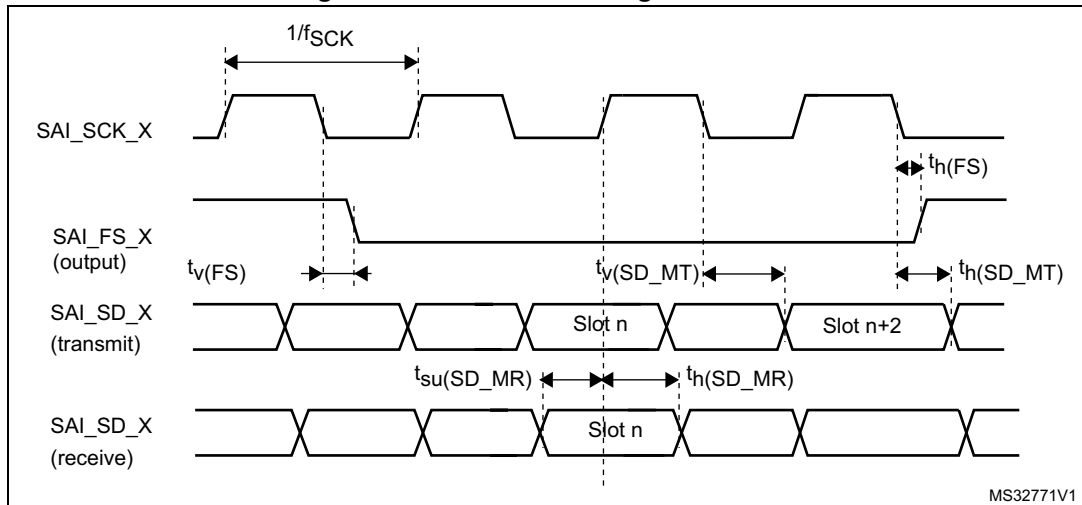
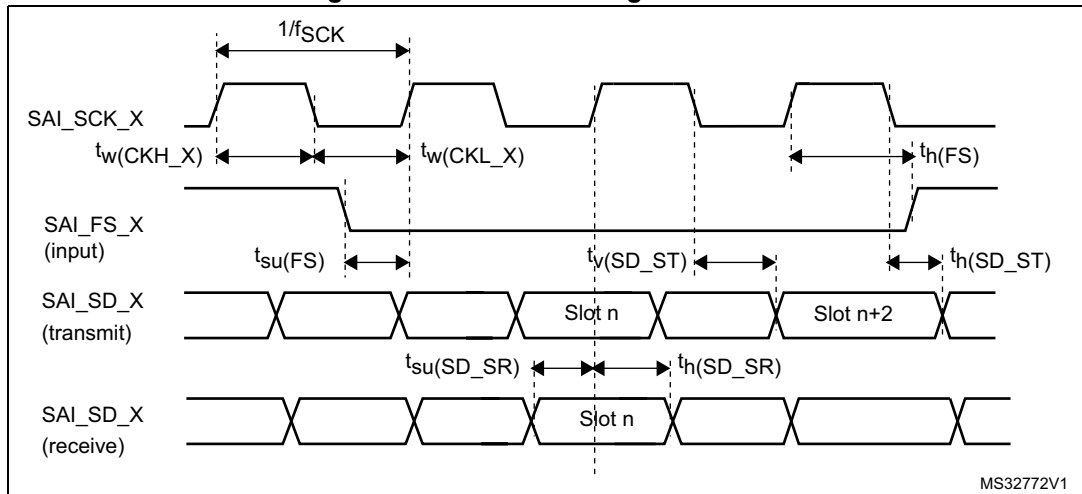


Figure 54. SAI slave timing waveforms



MDIO characteristics

Table 106. MDIO Slave timing parameters

Symbol	Parameter	Min	Typ	Max	Unit
F_{sDC}	Management data clock	-	-	40	MHz
$t_{d(MDIO)}$	Management data input/output output valid time	7	8	20	ns
$t_{su(MDIO)}$	Management data input/output setup time	4	-	-	
$t_{h(MDIO)}$	Management data input/output hold time	1	-	-	

The MDIO controller is mapped on APB2 domain. The frequency of the APB bus should at least 1.5 times the MDC frequency: $F_{PCLK2} \geq 1.5 * F_{MDC}$.

Table 116. LQPF100 - 100-pin, 14 x 14 mm low-profile quad flat package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	15.800	16.000	16.200	0.6220	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591
D3	-	12.000	-	-	0.4724	-
E	15.800	16.000	16.200	0.6220	0.6299	0.6378
E1	13.800	14.000	14.200	0.5433	0.5512	0.5591
E3	-	12.000	-	-	0.4724	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0.0°	3.5°	7.0°	0.0°	3.5°	7.0°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.